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## **TEE403**

(Following Paper ID a	and Roll No	to be fi	lled in y	our A	nswe	r Book)	A COMPANY OF THE OWNER OWNE
PAPER ID : 2053	Roll No.						Concession of the local division of the loca

## B. Tech.

# (SEM. IV) THEORY EXAMINATION 2010-11 ELECTRICAL AND ELECTRONICS ENGG. MATERIALS

## Time : 3 Hours

Total Marks: 100

Note : Attempt all questions.

1. Attempt any four parts of the following : (4×5=20)

(a) What is forbidden energy gap ? Classify insulators, semiconductors and conductors on the basis of energy band diagram.

(b) Describe briefly the basic seven crystal systems.

- (c) Explain Bragg's Law. How it can be used to determine the lattice parameters ?
- (d) Discuss briefly:
  - (i) Schottky defects and
  - (ii) Frenkel defects.
- (e) Explain, space lattice and Atomic packing factor.
- (f) Explain briefly:
  - (i) Body centred cubic structure (BCC)
  - (ii) Face centred cubic structure (FCC).

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2. Attempt any **four** parts of the following :

 $(4 \times 5 = 20)$ 

- (a) Explain the different factors which affect the resistivity of conducting materials?
- (b) What is superconductivity? Discuss the effect of magnetic field on the superconductors.
- (c) Derive an expression for heat developed in a current carrying conductor.
- (d) Explain Seebeck, Peltier and Thomson effects.
- (e) Explain briefly Sommerfeld theory and Zone theory of solids.
- (f) A coil of copper wire has a resistance of 50 ohm at 20°C. Calculate its resistance at 60°C. Given the temperature
  \* \* \* coefficient of resistance at 0°C as 0.00427.
- 3. Attempt any two parts of the following:  $(2 \times 10 = 20)$ 
  - (a) What is Hall Effect ? Derive the relation between Hall coefficient and carrier density.
  - (b) Describe the construction and working principle of FET. How does it differ from IGFET ?
  - (c) (i) Differentiate between intrinsic and extrinsic semiconductors.
    - (ii) Discuss in brief the effect of temperature on the conductivity of N-type or P-type materials.
- 4. Attempt any two parts of the following: (2×10=20)
  - (a) Describe hystereris loop of a magnetic material and explain residual magnetism and coercive force.

- (b) (i) Differentiate between soft and hard magnetic materials.
  - (ii) Distinguish between diamagnetism, paramagnetisms and ferromagnetism.
- (c) Explain the following:
  - (i) Relative permealability
  - (ii) Magnetic susceptibility
  - (iii) Magnetostriction and
  - (iv) Magnetic anisotropy.
- 5. Attempt any two parts of the following:  $(2 \times 10 = 20)$ 
  - (a) What is dielectric loss and loss angle ? How do the loss factor and dielectric constant vary with temperature and frequency of an alternating field ? Explain.
  - (b) Describe various mechanisms of dielectric polarisation and derive an expression for electronic polarizability.
  - (c) (i) A simple parallel plate condenser is to be made to store 10 μc at a potential of 10 kv. The separation between the plates is to be 5×10<sup>-9</sup> m. Calculate the area that the plates must have if the dielectric material between the plates is of alumina of dielectric constant 10.
    - (ii) Prove that the internal field due to polarization inside the dielectric is given by :

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$$t^1 = E + \frac{P}{3\xi_o}$$

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